Amendments to the Specification:

Please replace paragraph [69] on pages 24-25 with the following amended paragraph:

[69] An additional problem that must be solved before a successful industrial system is implemented is the prevention of redeposition of removed particles. The most fundamental requirement for redeposition prevention is that the velocity of the particle be greater than the escape velocity. As soon as the particle has been removed from the surface, it is subject to drag forces from the surrounding atmosphere and these retarding forces are more significant for smaller particles. Two solutions have been proposed and implemented to some degree - reduce the pressure of the surrounding ambient to increase the mean free path of the removed particle, or use a gas jet parallel to the surface to entrain the removed particle. It has also been suggested that the particles could be ionized and trapped electrostatically. Co-pending application Serial No. ~~[Attorney Docket No. FSU-0004]~~ 09/909,992, now, U.S. Patent No. 6,805,751, which is hereby incorporated by reference, discloses using thermophoresis to prevent redeposition of particles. Alternatively, a cold plate in a vacuum or low pressure ambient could be provided to draw removed particles (and any ETM) away from the surface and prevent them from redepositing. In any event, redeposition is another issue that much be addressed when utilizing LAPR.

Please replace paragraph [116] on page 43 with the following amended paragraph:

[116] The particle gun 200 of Figure 13 includes a radiation source 205, a flat and transparent substrate 220 coated by an ETM 223. The particles 222 are distributed across the substrate 220 in a pattern where the density of particles 222 is greater towards the periphery of the substrate 220. Other particle density distributions can also be achieved. Particle density distribution can also include distributions based on particle size, mass, shape, charge, composition, etc. The particle gun 200 has its laser energy source 205 behind the substrate 220 relative to the particles 222, and also includes an aperture 249 and focusing means 248. The particle gun 200 irradiates the substrate 220, which heats the ETM 223 by conduction launching the particles [[122]] 222 away from the surface of the substrate 220, and depositing the particles onto ~~target~~ a target substrate 240.